

Embedded OEM

DRAM

DDR3

DDR2

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DRAM DDR3

SODIMM

RDIMM	UDIMM	SODIMM	mini DIMM
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DDR3 is the current mainstream dram technology standardized by JEDEC, bringing further improvements in power consumption and increased bandwidth over DDR2. Available in power supply voltages of 1.5V (DDR3) and 1.35V (DDR3L) and with transfer data rates from 800Mb/s to 1.6Gb/s and beyond, DDR3 has become the de facto mainstream memory technology especially for server and notebook applications in the 1H of 2010. Many other applications are available in the market today to take advantage of the superior performance features of DDR3 and DDR3L. Wintec currently offers following DDR3 and DDR3L Modules and will continue to add more solutions as DDR3/DDR3L enabled applications will proliferate.

DDR3 - 204-Pin SODIMM - Registered ECC

Standard Profile (1.181") with Nominal Voltage (1.5V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
1GB	WD3AE01GX809-xxxx-yyz	1 rank	128x72	128Mx8	1.5V
2GB	WD3AE02GX809-xxxx-yyz	1 rank	256x72	256Mx8	1.5V
	WD3AE02GX818-xxxx-yyz	2 rank	256x72	128Mx8	1.5V
4GB	WD3AE02GX418-xxxx-yyz	2 rank	512x72	256Mx8	1.5V
	WD3AE04GX436-xxxx-yyz	1 rank	512x72	512Mx8	1.5V

DDR3 - 204-Pin SODIMM - Unbuffered ECC

Standard Profile (1.181") with Nominal Voltage (1.5V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage

1GB	WD3SE01GX809-xxxxx-yy	1 rank	128x72	128Mx8	1.5V
2GB	WD3SE02GX809-xxxxx-yy	1 rank	256x72	256Mx8	1.5V
	WD3SE02GX818-xxxxx-yy	2 rank	128x72	128Mx8	1.5V
4GB	WD3SE04GX818-xxxxx-yy	2 rank	512x72	256Mx8	1.5V
	WD3SE04GX809-xxxxx-yy	1 rank	512x72	512Mx8	1.5V
8GB	WD3SE08GX818-xxxxx-yy	2 rank	1024x72	512Mx8	1.5V

DDR3 - 204-Pin SODIMM - Unbuffered Non-ECC

Standard Profile (1.181") with Nominal Voltage (1.5V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
1GB	WD3SN01GX808-xxxxx-yy	1 rank	128x64	128Mx8	1.5V
2GB	WD3SN02GX808-xxxxx-yy	1 rank	256x64	256Mx8	1.5V
	WD3SN02GX816-xxxxx-yy	2 rank	256x64	128Mx8	1.5V
4GB	WD3SN04GX816-xxxxx-yy	2 rank	512x64	256Mx8	1.5V
	WD3SN04GX808-xxxxx-yy	1 rank	512x64	512Mx8	1.5V

(xxxx) Module speed (MHz) and Cas Latency

= 1066J : 1066MHz CL 7
1333L : 1333Mhz CL9
1600N :1600MHz CL11

DRAM Manufacturer and Die Revision

(yy) = P: Samsung A: A-Die
H: Micron B: B-Die
C: Hynix C: C-Die

Buffer / Register set (Only applies to Registered/Buffered modules)

(z) = I: Inphi
D: IDT
L: Intel